NSN 5962-01-305-6306

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-305-6306 **Body Length:** 0.840 inches **Body Width:** 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 739.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Monolithic and bipolar and schottky and programmable and w/active pull-up **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Case Outline Source And Designator:** D-2 mil-m-38510 **Terminal Surface Treatment:** Solder **Voltage Rating And Type Per Characteristic:** 7.0 volts power source **Time Rating Per Chacteristic:** 35.00 nanoseconds propagation delay time, low to high level output and 35.00 nanoseconds propagation delay time, high to low level output **Memory Device Type:** Rom **Test Data Document:** 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). **Terminal Type And Quantity:** 16 printed circuit Shelf Life: N/a **Unit Of Measure:**

Demilitarization:

Yes - demil/mli

NSN 5962-01-305-6306

Memory Microcircuit - Page 2 of 2



Fiig:

A458a0